Erratum: Calorimetry of hydrogen desorption from *a*-Si nanoparticles [Phys. Rev. B 65, 115403 (2002)]

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We made an arithmetic error in the calculation of the formation energy of one dangling bond, E(DB), by using Eq. (4) with the data detailed in the text below it. If the energy of one Si-H group is taken as $E(\text{Si-H}) = 3.25$ eV/(H atom), then Eq. (4) delivers an E(DB) value of 1.04 eV, instead of the 1.15 eV writen in the paper. This modification should be transmitted to the last line of the abstract and conclusions section where, in view of the accuracy of the data, we must conclude that $E(\text{DB}) = 1.05 \pm 0.10$ eV (instead of 1.15). Additionally, the last paragraph of Sec. IV should be modified accordingly and should say that the dangling bond energy of formation is slightly lower than the value that would be obtained when considering the energy of formation of monoatomic Si gas [4.66 eV/(Si atom)].

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